

# $2\Omega$ CMOS $\pm$ 5 V/5 V, SPST Switches

### ADG601/ADG602

#### **FEATURES**

Low On Resistance 2.5  $\Omega$  Max <0.6  $\Omega$  On Resistance Flatness Dual ±2.7 V to ±5.5 V or Single 2.7 V to 5.5 V Supplies Rail-to-Rail Input Signal Range Tiny 6-Lead SOT-23 and 8-Lead MSOP Packages **Low Power Consumption** TTL/CMOS Compatible Inputs

#### **APPLICATIONS Automatic Test Equipment Power Routing Communication Systems Data Acquisition Systems** Sample and Hold Systems **Avionics Relay Replacement Battery-Powered Systems**

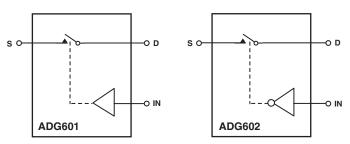
#### **GENERAL DESCRIPTION**

The ADG601/ADG602 are monolithic CMOS SPST (single pole, single throw) switches with on resistance typically less than  $2.5 \Omega$ . The low on resistance flatness makes the ADG601/ADG602 ideally suited to many applications, particularly those requiring low distortion. These switches are ideal for replacements for mechanical relays because they are more reliable and have lower power requirements and a much smaller package size.

The ADG601 is a normally open (NO) switch, while the ADG602 is normally closed (NC). Each switch conducts equally well in both directions when ON, with the input signal range extending to the supply rails.

The switches are available in tiny 6-lead SOT-23 and 8-lead MSOP packages.

#### FUNCTIONAL BLOCK DIAGRAMS



SWITCHES SHOWN FOR A LOGIC 1 INPUT

Table I. Truth Table

ADG601 In	ADG602 In	Switch Condition
0	1	OFF
1	0	ON

#### PRODUCT HIGHLIGHTS

- 1. Low On Resistance (2  $\Omega$  typical).
- 2. Dual  $\pm 2.7$  V to  $\pm 5.5$  V or Single 2.7 V to 5.5 V Supplies.
- 3. Tiny 6-lead SOT-23 and 8-lead MSOP Packages.
- 4. Rail-to-Rail Input Signal Range.

#### REV. A

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# ADG601/ADG602-SPECIFICATIONS

**DUAL SUPPLY**  $(V_{DD} = 5 \text{ V} \pm 10\%, V_{SS} = -5 \text{ V} \pm 10\%, \text{ GND} = 0 \text{ V}, \text{ unless otherwise noted.})$ 

Parameter	+25°C	Version -40°C to +85°C	Unit	Test Conditions/Comments
ANALOG SWITCH				
Analog Signal Range		$ m V_{SS}$ to $ m V_{DD}$	V	
On Resistance (R <sub>ON</sub> )	2 2.5	5.5	$\Omega$ typ $\Omega$ max	$V_{\rm DD}$ = +4.5 V, $V_{\rm SS}$ = -4.5 V $V_{\rm S}$ = ±4.5 V, $I_{\rm S}$ = -10 mA; Test Circuit 1
On Resistance Flatness (R <sub>FLAT (ON)</sub> )	0.35 0.5	0.4 0.6	$\Omega$ typ $\Omega$ max	$V_S = \pm 3.3 \text{ V}, I_S = -10 \text{ mA}$
LEAKAGE CURRENTS				
Source OFF Leakage I <sub>S</sub> (OFF)	±0.01 ±0.25	±1	nA typ nA max	$V_{\rm DD}$ = +5.5 V, $V_{\rm SS}$ = -5.5 V $V_{\rm S}$ = +4.5 V/-4.5 V, $V_{\rm D}$ = -4.5 V/+4.5 V; Test Circuit 2
Drain OFF Leakage I <sub>D</sub> (OFF)	±0.01 ±0.25	±1	nA typ nA max	$V_S = +4.5 \text{ V/}-4.5 \text{ V}, V_D = -4.5 \text{ V/}+4.5 \text{ V};$ Test Circuit 2
Channel ON Leakage I <sub>D</sub> , I <sub>S</sub> (ON)	±0.01 ±0.25	±1	nA typ nA max	$V_S = V_D = +4.5 \text{ V or } -4.5 \text{ V};$ Test Circuit 3
DIGITAL INPUTS Input High Voltage, V <sub>INH</sub> Input Low Voltage, V <sub>INL</sub> Input Current		2.4 0.8	V min V max	
$I_{INL}$ or $I_{INH}$	0.005	±0.1	μA typ μA max	$V_{IN} = V_{INL}$ or $V_{INH}$
C <sub>IN</sub> , Digital Input Capacitance	2		pF typ	
DYNAMIC CHARACTERISTICS <sup>2</sup>				
$t_{ON}$	80 120	155	ns typ ns max	$R_L = 300 \Omega$ , $C_L = 35 pF$ $V_S = 3.3 V$ ; Test Circuit 4
$t_{\mathrm{OFF}}$	45 75	90	ns typ ns max	$R_L = 300 \Omega$ , $C_L = 35 pF$ $V_S = 3.3 V$ ; Test Circuit 4
Charge Injection	250		pC typ	$V_S = 0 \text{ V}, R_S = 0 \Omega, C_L = 1 \text{ nF}; \text{ Test Circuit 5}$
Off Isolation Bandwidth –3 dB	-60 180		dB typ MHz typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$ ; Test Circuit 6 $R_L = 50 \Omega$ , $C_L = 5 pF$ ; Test Circuit 7
C <sub>S</sub> (OFF)	50		pF typ	f = 1  MHz
$C_{\rm D}$ (OFF)	50		pF typ	f = 1  MHz
$C_{D}$ , $C_{S}$ (ON)	145		pF typ	f = 1 MHz
POWER REQUIREMENTS				
				$V_{DD} = +5.5 \text{ V}, V_{SS} = -5.5 \text{ V}$
$I_{DD}$	0.001	1.0	μΑ typ μΑ max	Digital Inputs = 0 V or 5.5 V
$I_{SS}$	0.001	1.0	μΑ typ μΑ max	Digital Inputs = 0 V or 5.5 V

#### NOTES

Specifications subject to change without notice.

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 $<sup>^1</sup>Temperature$  range is as follows: B Version:  $-40^{\circ}C$  to  $+85^{\circ}C.$ 

<sup>&</sup>lt;sup>2</sup>Guaranteed by design, not subject to production test.

# SINGLE SUPPLY $^1$ (V $_{DD}$ = 5 V $\pm$ 10%, V $_{SS}$ = 0 V, GND = 0 V, unless otherwise noted.)

B Version				
Parameter	+25°C	-40°C to +85°C	Unit	Test Conditions/Comments
ANALOG SWITCH				
Analog Signal Range		0 V to V <sub>DD</sub>	V	
		22		$V_{\mathrm{DD}} = 4.5  \mathrm{V}$
On Resistance (R <sub>ON</sub> )	3.5		Ω typ	$V_S = 0 \text{ V to } 4.5 \text{ V}, I_S = -10 \text{ mA};$
	5	8	Ω max	Test Circuit 1
On Resistance Flatness (R <sub>FLAT (ON)</sub> )	0.2	0.2	Ω typ	$V_S = 1.5 \text{ V to } 3.3 \text{ V}, I_S = -10 \text{ mA}$
		0.35	Ω max	
LEAKAGE CURRENTS				
				$V_{\rm DD} = 5.5 \text{ V}$
Source OFF Leakage I <sub>S</sub> (OFF)	±0.01		nA typ	$V_S = 4.5 \text{ V/1 V}, V_D = 1 \text{ V/4.5 V};$
	±0.25	±1	nA max	Test Circuit 2
Drain OFF Leakage I <sub>D</sub> (OFF)	±0.01		nA typ	$V_S = 4.5 \text{ V/1 V}, V_D = 1 \text{ V/4.5 V};$
5 - 1	±0.25	±1	nA max	Test Circuit 2
Channel ON Leakage ID, IS (ON)	±0.01		nA typ	$V_S = V_D = 4.5 \text{ V or } 1 \text{ V};$
	±0.25	±1	nA max	Test Circuit 3
DIGITAL INPUTS				
Input High Voltage, V <sub>INH</sub>		2.4	V min	
Input Low Voltage, V <sub>INL</sub>		0.8	V max	
Input Current				
I <sub>INL</sub> or I <sub>INH</sub>	0.005		μA typ	$V_{IN} = V_{INI}$ or $V_{INH}$
11.2		$\pm 0.1$	μA max	
C <sub>IN</sub> , Digital Input Capacitance	2		pF typ	
DYNAMIC CHARACTERISTICS <sup>2</sup>				
$t_{\mathrm{ON}}$	110		ns typ	$R_{L} = 300 \Omega, C_{L} = 35 pF$
	220	280	ns max	$V_S = 3.3 \text{ V}$ ; Test Circuit 4
t <sub>OFF</sub>	50		ns typ	$R_{L} = 300 \Omega, C_{L} = 35 \mathrm{pF}$
011	80	110	ns max	$V_S = 3.3 \text{ V}$ ; Test Circuit 4
Charge Injection	20		pC typ	$V_S = 0 \text{ V}, R_S = 0 \Omega, C_L = 1 \text{ nF}; \text{ Test Circuit 5}$
Off Isolation	-60		dB typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$ ; Test Circuit 6
Bandwidth –3 dB	180		MHz typ	$R_L = 50 \Omega$ , $C_L = 5 pF$ ; Test Circuit 7
$C_{S}$ (OFF)	50		pF typ	f = 1 MHz
$C_D$ (OFF)	50		pF typ	f = 1  MHz
$C_D$ , $C_S$ (ON)	145		pF typ	f = 1  MHz
POWER REQUIREMENTS				
Ţ	0.001		u A tree	$V_{DD} = 5.5 \text{ V}$
$I_{DD}$	0.001	1.0	μΑ typ μΑ max	Digital Inputs = 0 V or 5.5 V
		1.0	μαιπαχ	

#### NOTES

Specifications subject to change without notice.

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 $<sup>^{1}</sup>Temperature$  range is as follows: B Version: –40  $^{\circ}C$  to +85  $^{\circ}C.$ 

<sup>&</sup>lt;sup>2</sup>Guaranteed by design, not subject to production test.

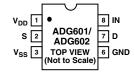
#### ABSOLUTE MAXIMUM RATINGS1

$(T_A = 25^{\circ}C, \text{ unless otherwise noted.})$
$V_{DD}$ to $V_{SS}$
V <sub>DD</sub> to GND
V <sub>SS</sub> to GND +0.3 V to -6.5 V
Analog Inputs <sup>2</sup> $V_{SS}$ – 0.3 V to $V_{DD}$ + 0.3 V
Digital Inputs <sup>2</sup> $-0.3 \text{ V}$ to $V_{DD} + 0.3 \text{ V}$
or 30 mA, whichever occurs first
Continuous Current, S or D 100 mA
Peak Current, S or D
(Pulsed at 1 ms, 10% Duty Cycle Max) 200 mA
Operating Temperature Range
Industrial (B Version)40°C to +85°C
Storage Temperature Range65°C to +150°C
Junction Temperature 150°C
MSOP Package
$\theta_{JA}$ Thermal Impedance
$\theta_{JC}$ Thermal Impedance
SOT-23 Package
$\theta_{JA}$ Thermal Impedance
$\theta_{JC}$ Thermal Impedance 91.99°C/W
Lead Temperature, Soldering (10 sec) 300°C
IR Reflow, Peak Temperature 220°C

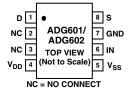
#### NOTES

#### PIN CONFIGURATIONS

6-Lead SOT-23 (RT-6)



8-Lead MSOP (RM-8)



#### ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option	Branding Information*
ADG601BRT-REEL	−40°C to +85°C	Plastic Surface-Mount Package (SOT-23)	RT-6	STB
ADG601BRT-REEL7	−40°C to +85°C	Plastic Surface-Mount Package (SOT-23)	RT-6	STB
ADG601BRM	−40°C to +85°C	Micro Small Outline Package (MSOP)	RM-8	STB
ADG601BRM-REEL	−40°C to +85°C	Micro Small Outline Package (MSOP)	RM-8	STB
ADG601BRM-REEL7	−40°C to +85°C	Micro Small Outline Package (MSOP)	RM-8	STB
ADG602BRT-REEL	−40°C to +85°C	Plastic Surface-Mount Package (SOT-23)	RT-6	SUB
ADG602BRT-REEL7	−40°C to +85°C	Plastic Surface-Mount Package (SOT-23)	RT-6	SUB
ADG602BRM	−40°C to +85°C	Micro Small Outline Package (MSOP)	RM-8	SUB
ADG602BRM-REEL	−40°C to +85°C	Micro Small Outline Package (MSOP)	RM-8	SUB
ADG602BRM-REEL7	−40°C to +85°C	Micro Small Outline Package (MSOP)	RM-8	SUB

<sup>\*</sup>Branding on SOT-23 and MSOP packages is limited to three characters due to space constraints.

#### CAUTION\_

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the ADG601/ADG602 features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



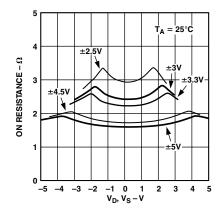
<sup>&</sup>lt;sup>1</sup> Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Only one absolute maximum rating may be applied at any one time.

<sup>&</sup>lt;sup>2</sup>Overvoltages at IN, S, or D will be clamped by internal diodes. Current should be limited to the maximum ratings given.

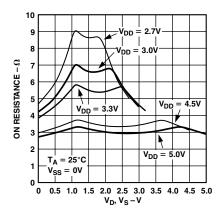
#### **TERMINOLOGY**

$\overline{\mathrm{V}_{\mathrm{DD}}}$	Most Positive Power Supply Potential.
$V_{SS}$	Most Negative Power Supply Potential.
$I_{ m DD}$	Positive Supply Current.
$I_{SS}$	Negative Supply Current.
GND	Ground (0 V) Reference.
S	Source Terminal. May be an input or output.
D	Drain Terminal. May be an input or output.
IN	Logic Control Input.
$V_{D}(V_{S})$	Analog Voltage on Terminals D, S.
$R_{ON}$	Ohmic Resistance between D and S.
R <sub>FLAT (ON)</sub>	Flatness is defined as the difference between the maximum and minimum values of on resistance as measured
	over the specified analog signal range.
$I_{S}$ (OFF)	Source Leakage Current with the Switch OFF.
$I_D$ (OFF)	Drain Leakage Current with the Switch OFF.
$I_D$ , $I_S$ (ON)	Channel Leakage Current with the Switch ON.
$V_{INL}$	Maximum Input Voltage for Logic 0.
$V_{INH}$	Minimum Input Voltage for Logic 1.
$I_{INL}(I_{INH})$	Input Current of the Digital Input.
$C_{S}$ (OFF)	OFF Switch Source Capacitance. Measured with reference to ground.
$C_D$ (OFF)	OFF Switch Drain Capacitance. Measured with reference to ground.
$C_D, C_S(ON)$	ON Switch Capacitance. Measured with reference to ground.
$C_{IN}$	Digital Input Capacitance.
$t_{ON}$	Delay between applying the digital control input and the output switching ON.
$t_{OFF}$	Delay between applying the digital control input and the output switching OFF.
Charge Injection	A measure of the glitch impulse transferred from the digital input to the analog output during switching.
Off Isolation	A measure of unwanted signal coupling through an OFF switch.
On Response	Frequency response of the ON switch.
Insertion Loss	Loss due to the ON resistance of the switch.

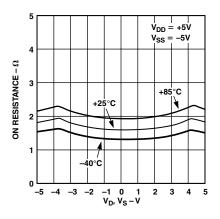
# **Typical Performance Characteristics**



TPC 1. On Resistance vs.  $V_D(V_S)$  (Dual Supply)

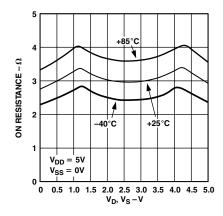


TPC 2. On Resistance vs.  $V_D(V_S)$  (Single Supply)

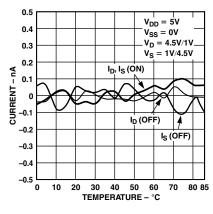


TPC 3. On Resistance vs.  $V_D(V_S)$  for Different Temperatures (Dual Supply)

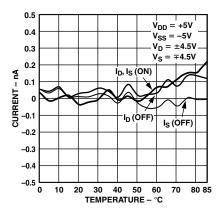
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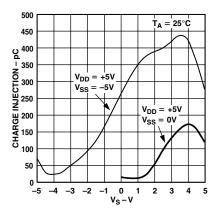
TPC 4. On Resistance vs.  $V_D(V_S)$  for Different Temperatures (Single Supply)



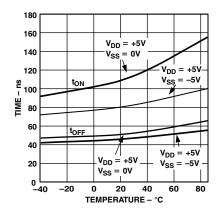
TPC 5. Leakage Currents vs. Temperature (Single Supply)



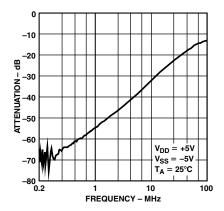
TPC 6. Leakage Currents vs. Temperature (Dual Supply)



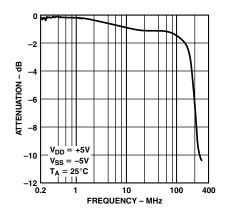
TPC 7. Charge Injection vs. Source Voltage



TPC 8.  $t_{ON}/t_{OFF}$  Times vs. Temperature



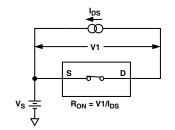
TPC 9. Off Isolation vs. Frequency

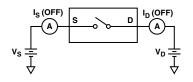


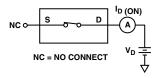
TPC 10. On Response vs. Frequency

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#### **TEST CIRCUITS**



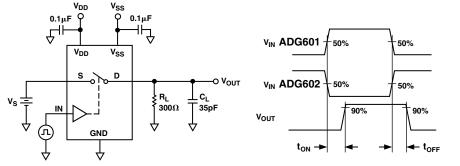




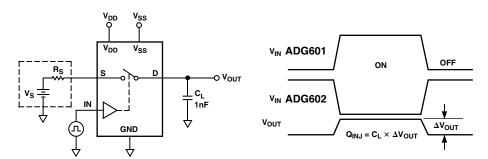
Test Circuit 1. On Resistance

Test Circuit 2. Off Leakage

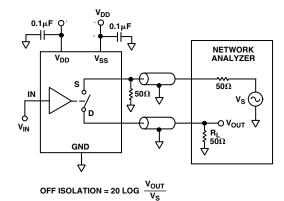
Test Circuit 3. On Leakage



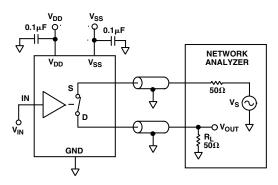
Test Circuit 4. Switching Times



Test Circuit 5. Charge Injection



Test Circuit 6. Off Isolation



 $\label{eq:output} \text{INSERTION LOSS} = 20 \text{ LOG} \ \frac{\text{V}_{\text{OUT}} \text{ WITH SWITCH}}{\text{V}_{\text{S}} \text{ WITHOUT SWITCH}}$ 

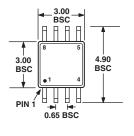
Test Circuit 7. Bandwidth

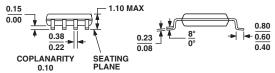
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#### **OUTLINE DIMENSIONS**

# 8-Lead Mini Small Outline Package [MSOP] (RM-8)

Dimensions shown in millimeters

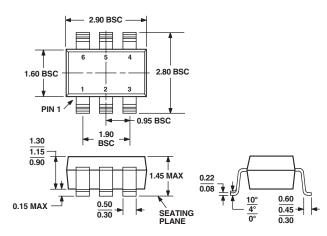




COMPLIANT TO JEDEC STANDARDS MO-187AA

### 6-Lead Small Outline Transistor Package [SOT-23] (RT-6)

Dimensions shown in millimeters



COMPLIANT TO JEDEC STANDARDS MO-178AB

## **Revision History**

Location	Page
6/03—Data Sheet changed from REV. 0 to REV. A	
Changes to SPECIFICATIONS	2
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Updated OUTLINE DIMENSIONS	8

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